Central Semiconductor Corp.
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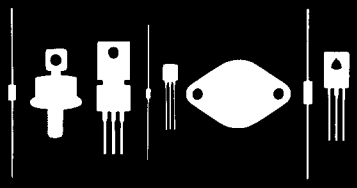

2N524 THRU 2N527

PNP GERMANIUM TRANSISTORS

JEDEC TO-5 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N524 series types are germanium PNP transistors designed for low frequency medium power amplifier and switching applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNIT
Collector-Base Voltage	V_{CBO}	45	V
Collector-Emitter Voltage	V_{CER}	30	V
Emitter-Base Voltage	V_{EBO}	15	V
Collector Current	I_C	500	mA
Emitter Current	I_E	500	mA
Power Dissipation	P_D	225	mW
Operating and Storage Junction Temperature	T_J T_{STG}	-65 to +100	°C
Thermal Resistance	ΘJA	33.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{CBO}	V_{CB}=30V		10	μA
I_{EBO}	V_{EB}=15V		10	μA
BV_{CBO}	I_C=200μA	45		V
BV_{CER}	I_C=600μA, R_{BE}=10kΩ	30		V
$V_{CE(SAT)}$	I_C=20mA, I_B=2.0mA (2N524)		130	mV
$V_{CE(SAT)}$	I_C=20mA, I_B=1.33mA (2N525)		130	mV
$V_{CE(SAT)}$	I_C=20mA, I_B=1.0mA (2N526)		130	mV
$V_{CE(SAT)}$	I_C=20mA, I_B=0.67mA (2N527)		130	mV
$V_{BE(ON)}$	V_{CE}=1.0V, I_C=20mA (2N524)	220	320	mV
$V_{BE(ON)}$	V_{CE}=1.0V, I_C=20mA (2N525)	200	300	mV
$V_{BE(ON)}$	V_{CE}=1.0V, I_C=20mA (2N526)	190	280	mV
$V_{BE(ON)}$	V_{CE}=1.0V, I_C=20mA (2N527)	180	260	mV
h_{FE}	V_{CE}=1.0V, I_C=20mA (2N524)	25	42	
h_{FE}	V_{CE}=1.0V, I_C=20mA (2N525)	34	65	
h_{FE}	V_{CE}=1.0V, I_C=20mA (2N526)	53	90	
h_{FE}	V_{CE}=1.0V, I_C=20mA (2N527)	72	121	
C_{ob}	V_{CB}=5.0V, I_C=0, f=1.0MHz	5.0	40	pF
NF	V_{CB}=5.0V, R_G=1.0kΩ, BW=1.0Hz, f=1.0kHz	-	15	db

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